

225mW Surface Mount Switching Diode-70V

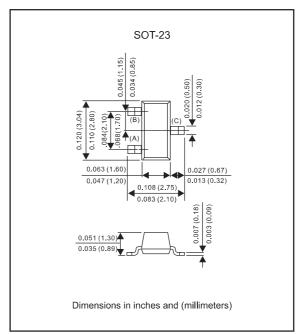
Features

- Fast speed switching.
- For general purpose switching application.
- High conductance.
- Silicon epitaxial planar chip.
- Lead-free parts meet RoHS requirments.
- Suffix "-H" indicates Halogen-free part, ex.BAL99-H.

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-23
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any

Package outline



Maximum ratings (AT T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	BAL99	BAV99	BAW56	BAV70	UNIT
Reverse Voltage	V _R	70				V
Forward Current	I _F	100	215	200		mA
Peak Forward Surge Current	I _{FM}	500				mA
Non-Repetitive Peak Forward Surge Current @ t=1.0us @ t=1.0s	I _{FSM}	2.0 1.0				A

Thermal Characteristics

PARAMETER		SYMBOL	MAX.	UNIT
Total Device Dissipation FR-5	Board* ¹ , T _A = 25 ^o C	Pn	225	mW
	Derate Above 25° C	ГD	1.8	mW/°C
Thermal Resistance Junction to Ambient			556	°C/W
Total Device Dissipation Alumina	Substrate ^{*2} , $T_A = 25^{\circ}C$	р	300	mW
	Derate Above 25° C	P _D	2.4	mW/°C
Thermal Resistance Junction to Ambient			417	°C/W
Operating Temperature Range		T	-55 ~ +150	°C
Storage Temperature Range		T _{STG}	-65 ~ +150	°C

 $1. FR-5 = 1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



 Document ID
 Issued Date
 Revised Date
 Revision
 Page.

 AS-3120033
 2003/03/08
 2012/05/16
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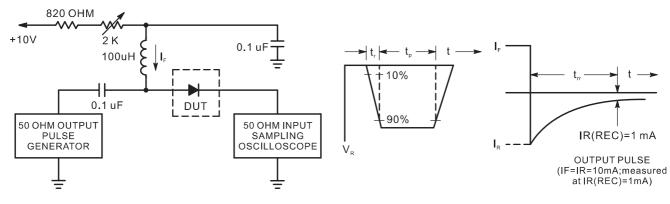


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Electrical Characteristics (AT T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Reverse Breakdown Voltage(I _{BR} =100uAdc)	V _{BR}	70		V
Reverse Voltage Leakage Current (at $V_R = 70V$, $T_J = 25^{\circ}C$)BAL99/BAV99/BAW56/BAV70 (at $V_R = 25V$, $T_J = 150^{\circ}C$)BAL99/BAV99/BAW56 (at $V_R = 25V$, $T_J = 150^{\circ}C$)BAV70 (at $V_R = 70V$, $T_J = 150^{\circ}C$)BAL99/BAV99/BAW56 (at $V_R = 70V$, $T_J = 150^{\circ}C$)BAV70	I _R		2.5 30 60 50 100	μΑ
Diode Capacition(V _R = 0V, f = 1.0MHz) BAL99/BAV99/BAV70 BAW56	C _D		1.5 2.0	pF
Reverse Recovery Time($I_F = I_R = 10mA$, $V_R = 5.0Vdc$, $I_R(REC) = 1.0mAdc$, $R_L = 100_{OHM}$)	t _{rr}		6.0	ns
Forward Voltage (at $I_F = 1.0 \text{mAdc}$) (at $I_F = 10 \text{mAdc}$) (at $I_F = 50 \text{mAdc}$) (at $I_F = 150 \text{mAdc}$)	V _F		715 855 1000 1250	mV

Recovery Time Equivalent Test Circuit

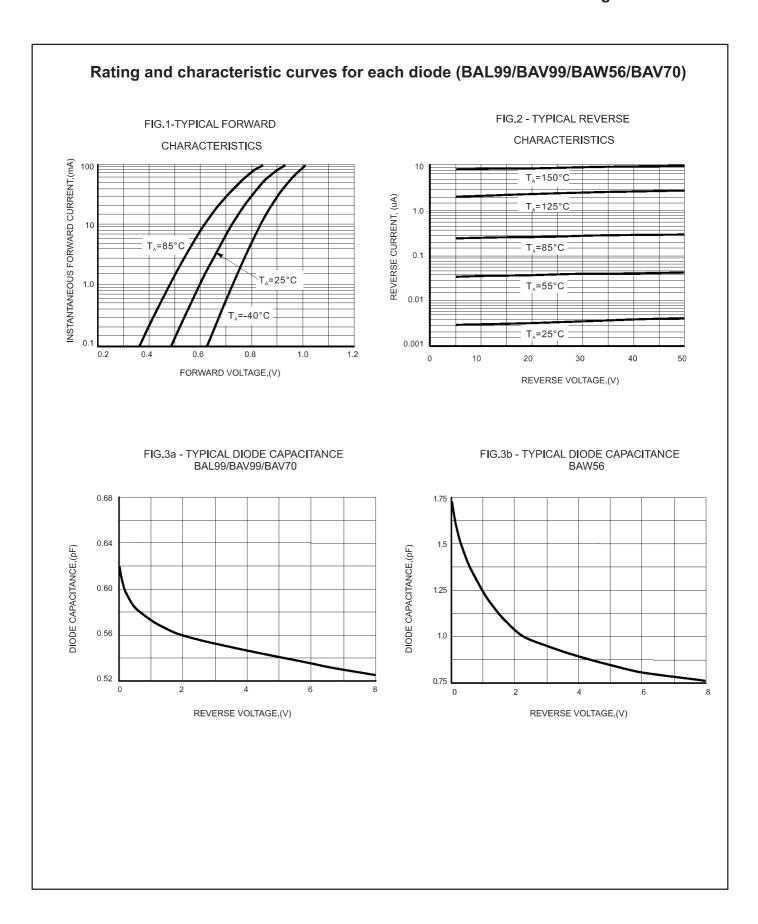


Notes : 1.A2.0 Kohm variable resistor adjusted for a forward Current (IF) of 10mA. 2. Input pulse is adjusted so IR(peak) is equal to 10 mA. 3. tp >> trr.





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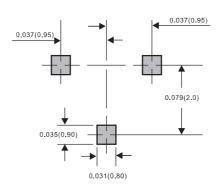
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Pinning information

Type number	Marking code	Symbol
BAL99	L4, A6, JF	
BAV99	JG, A7 *	
BAW56	JC, A1*	
BAV70	JA, A4 *	

Suggested solder pad layout

SOT-23



Dimensions in inches and (millimeters)

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-23	7"	3000	4.0	30,000	183*183*123	178	382*262*387	240,000	11.6



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